TEXAS INSTRUMENTS
Data sheet acquired from Harris Semiconductor
SCHS041D – Revised October 2003

CD4043B, CD4044B Types

CMOS Quad 3-State R/S Latches

High-Voltage Types (20-Volt Rating)
Quad NOR R/S Latch – CD4043B
Quad NAND R/S Latch – CD4044B

■CD4043B types are quad cross-coupled 3-state CMOS NOR latches and the CD4044B types are quad cross-coupled 3-state CMOS NAND latches. Each latch has a separate Q output and individual SET and RESET inputs. The Q outputs are controlled by a common ENABLE input. A logic "1" or high on the ENABLE input connects the latch states to the Q outputs. A logic "0" or low on the ENABLE input disconnects the latch states from the Q outputs, resulting in an open circuit condition on the Q outputs. The open circuit feature allows common bussing of the outputs.

The CD4043B and CD4044B types are supplied in 16-lead hermetic dual-in-line ceramic packages (F3A suffix), 16-lead dual-in-line plastic packages (E suffix), 16-lead small-outline packages (D, DR, DT, DW, DWR, and NSR suffixes), and 16-lead thin shrink small-outline packages (PW and PWR suffixes).

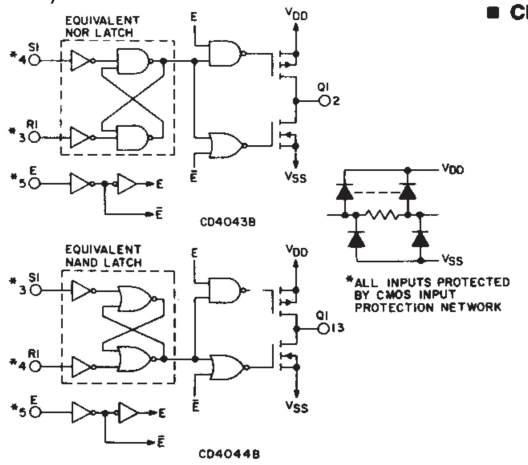


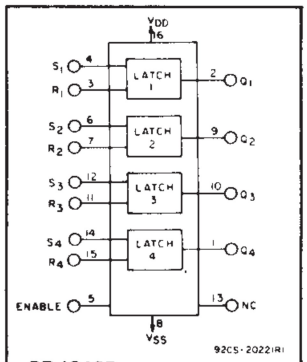
Fig. 1 – Logic diagrams.

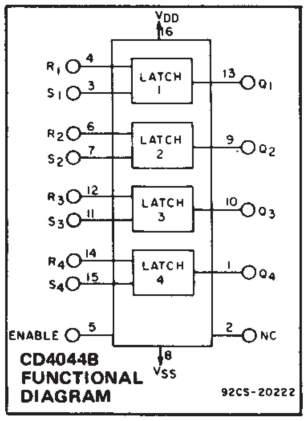
Features:

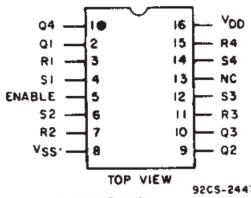
- 3-state outputs with common output ENABLE
- Separate SET and RESET inputs for each latch
- NOR and NAND configurations
- 5-V, 10-V, and 15-V parametric ratings
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range): 1 V at V_{DD} = 5 V; 2 V at V_{DD} = 10 V; 2.5 V at V_{DD} = 15 V
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

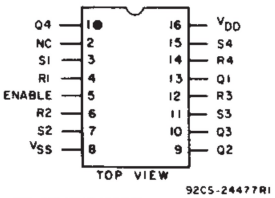
Applications:

- Holding register in multi-register system
- Four bits of independent storage with output ENABLE
- Strobed register
- General digital logic
- CD4043B for positive logic systems
- CD4044B for negative logic systems









TERMINAL ASSIGNMENTS

S	R	E	Q
X	X	0	OC*
0	0	1	NC+
1	0	1	1
0	1	1	0
1	1	1	Δ

*OPEN CIRCUIT
+ NO CHANGE
Δ DOMINATED BY S=1 INPUT
CD4043B

S	R	E	Q
X	X	0	OC*
1	1	1	NC+
0	1	1	1
1	0	1	0
0	0	1	ΔΔ

*OPEN CIRCUIT
+ NO CHANGE
ΔΔ DOMINATED BY R=0 INPUT
CD4044B

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

TRUTH TABLES

Recommended Operating Conditions T_A=25°C
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

Characteristic	V_{DD} (V)	Min.	Max.	Units
Supply-Voltage Range (T_A = Full Package Temperature Range)	–	3	18	V
SET or RESET Pulse Width, t_W	5	160	–	ns
	10	80	–	
	15	40	–	

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	1	1	30	30	–	0.02	1	μA
	–	0,10	10	2	2	60	60	–	0.02	2	
	–	0,15	15	4	4	120	120	–	0.02	4	
	–	0,20	20	20	20	600	600	–	0.04	20	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	0.5, 4.5	–	5	1.5				—	—	1.5	V
	1, 9	–	10	3				—	—	3	
	1.5,13.5	–	15	4				—	—	4	
Input High Voltage, V_{IH} Min.	0.5, 4.5	–	5	3.5				3.5	—	—	
	1, 9	–	10	7				7	—	—	
	1.5, 3.5	–	15	11				11	—	—	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA
3-State Output Leakage Current I_{OUT} Max.	0,18	0,18	18	±0.4	±0.4	±12	±12	–	$\pm 10^{-4}$	±0.4	μA

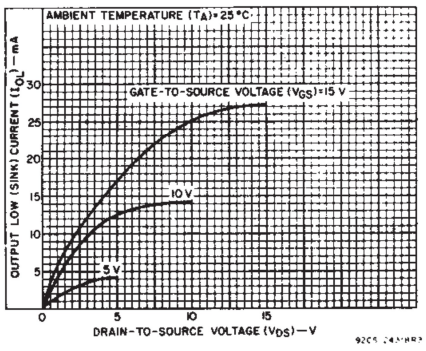


Fig. 2 — Typical output low (sink) current characteristics.

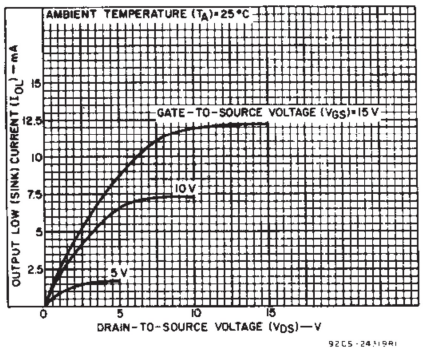


Fig. 3 — Minimum output low (sink) current characteristics.

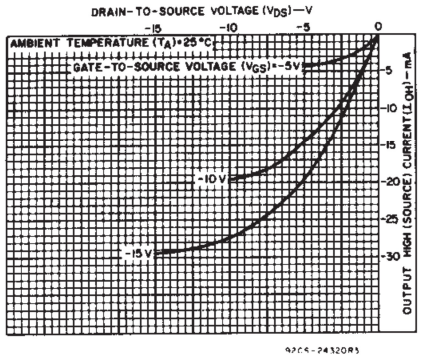


Fig. 4 — Typical output high (source) current characteristics.

DYNAMIC ELECTRICAL CHARACTERISTICS *at T_A = 25° C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 KΩ*

CHARACTERISTIC	V_{DD} (V)	LIMITS ALL TYPES TYP.	LIMITS ALL TYPES MAX.	UNITS
Propagation Delay Time: t_{PHL}, t_{PLH} SET or RESET to Q	5	150	300	ns
	10	70	140	
	15	50	100	
3-State Propagation Delay Time: ENABLE to Q t_{PHZ}, t_{PZH}	5	115	230	ns
	10	55	110	
	15	40	80	
t_{PLZ}, t_{PZL}	5	90	180	ns
	10	50	100	
	15	35	70	
Transition Time: t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Minimum SET or RESET Pulse Width, t_W	5	80	160	ns
	10	40	80	
	15	20	40	
Input Capacitance, (Any Input) C_{IN}	–	5	7.5	pF

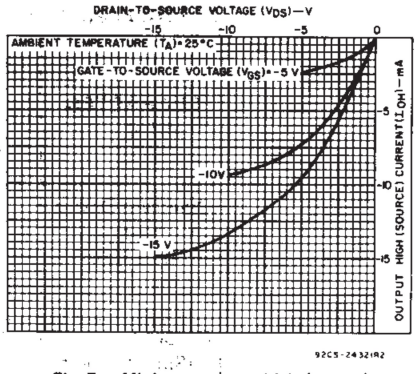


Fig. 5 – Minimum output high (source) current characteristics.

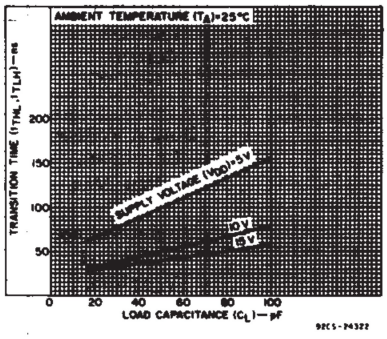


Fig. 6 – Typical transition time vs. load capacitance.

TEST CIRCUITS

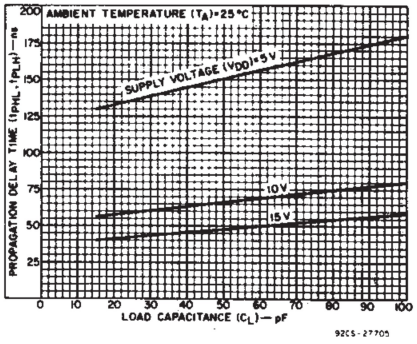


Fig. 7 – Typical propagation delay time vs. load capacitance—SET, RESET to Q, $\overline{Q}$.

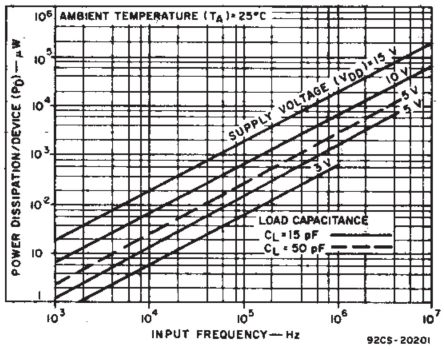


Fig. 8 – Typical power dissipation vs. frequency.

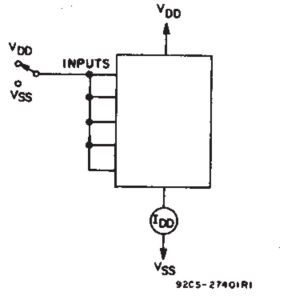


Fig. 9 – Quiescent device current.

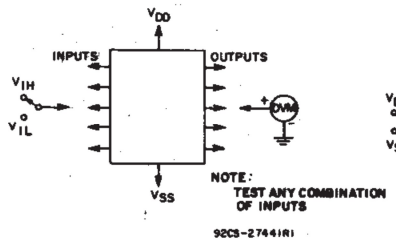


Fig. 10 – Input voltage.

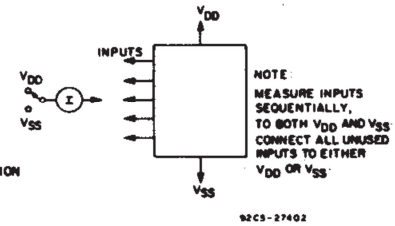


Fig. 11 – Input current.

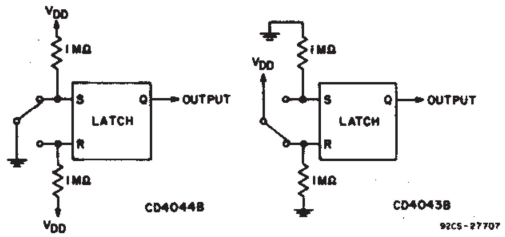


Fig. 12 – Switch bounce eliminator.

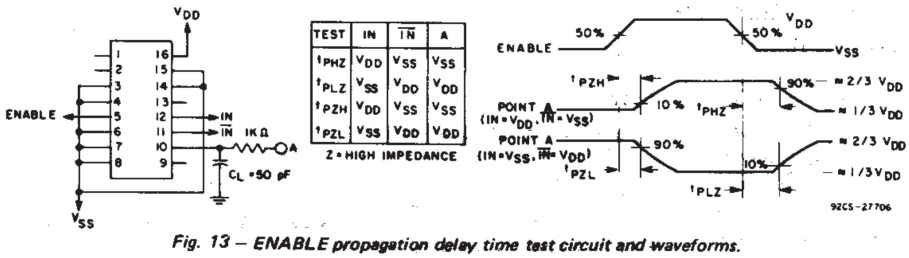
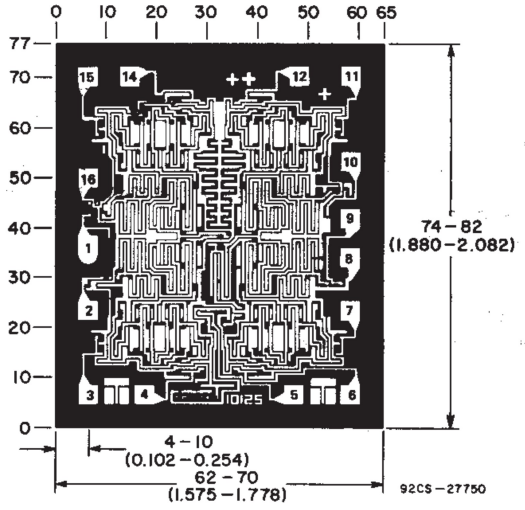
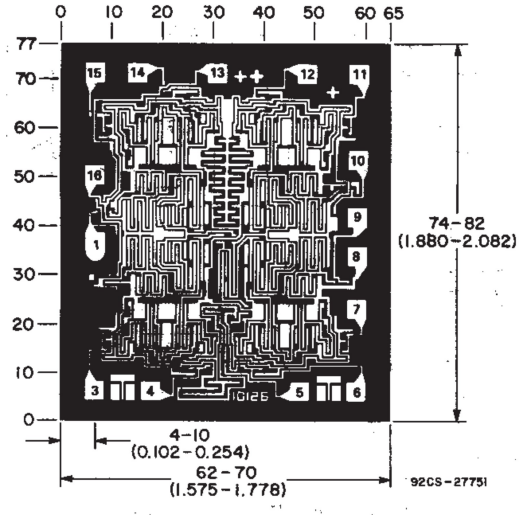


Fig. 13 – ENABLE propagation delay time test circuit and waveforms.

CHIP DIMENSIONS AND PAD LAYOUTS



CD4043BH



CD4044BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

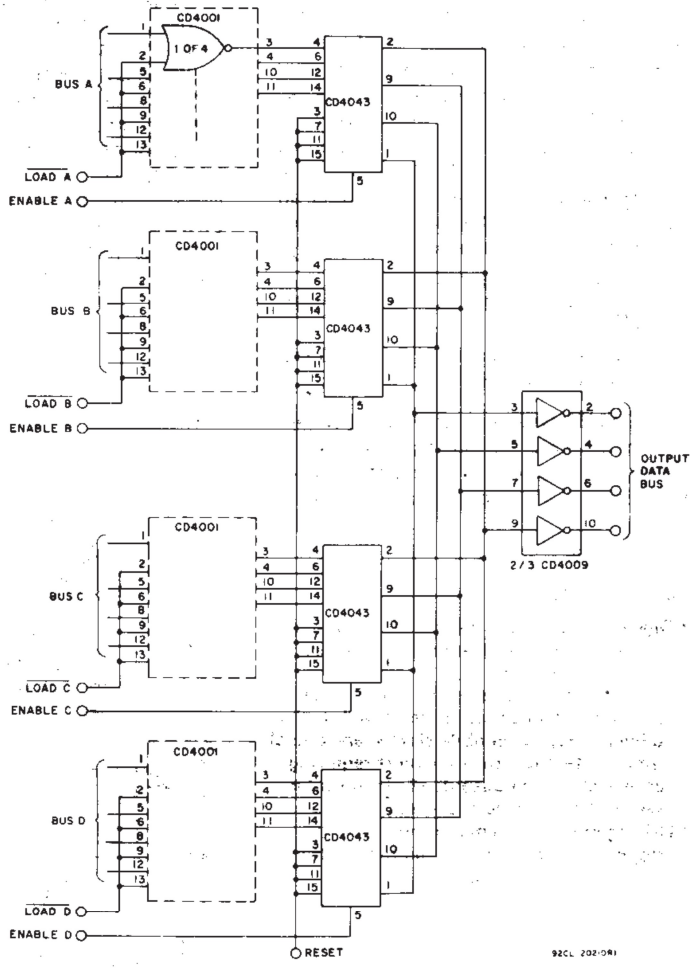


Fig. 14 – Multiple bus storage.